

Docket: CS 99 - 065

S/N: 09/442,499

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

Subject:

Divisional Application Based upon Parent Application Serial  
No.: 09/442,499, Filed: 11/18/99

Serial No. TBD

Inventor: Ho

Title: Plasma Etch Method For Forming Plasma Etched Silicon  
Layer

Group Art Unit: 1763

Examiner: Goudreau, G. A.

Attorney Docket: CS 99 - 065B

### PRELIMINARY AMENDMENT

Dear Sir:

In conjunction with the Divisional Application filed herewith,  
please consider the following remarks:

### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the  
United States Postal Service as first class mail in an envelope addressed to:

Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on \_\_\_\_  
October 27, 2003.

Signature/Date  10/27/03

Stephen B. Ackerman

Reg. No. 37,761

October 27, 2003

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile      Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

**Divisional Patent Application of**  
Serial No.: 09/442,499 11/18/99  
  
PAUL KWOK KEUNG HO, XUE CHUN DAI  
  
PLASMA ETCH METHOD FOR FORMING PLASMA  
ETCHED SILICON LAYER

**PRELIMINARY AMENDMENT**

Dear Sir:


This is a preliminary amendment for the above referenced Divisional Patent  
Application. Please amend the above identified application for patent as follows:

**CERTIFICATE OF MAILING**

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Postal Service as first class mail in an envelope addressed to: Commissioner of Patents  
and Trademarks, Washington, D.C. 20231, on October 27, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature/Date

 10/27/03